

IRFY Series Data Sheet

The IRFY Data Sheet describes 12 devices, 8 N-Channel and 4 P-Channel, all contained in the TO-257AB package. This data sheet is arranged to show common tabular and graphical information between devices.

Absolute maximum ratings and parametric data are presented in tabular format with devices grouped according to generically shared parameters. For each parametric rating, devices are categorized by N and P channel and listed in alpha-numeric order. The conditions specified for a given parametric test are provided in the right hand column of each table.

Graphical information is grouped by devices in

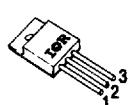
alphabetical order. Where the information is device specific, we have assigned a numeric character for the graph type and an alpha character to a given device. (See Table A below). Where graphs are polarity specific as in figures 10, 12, 14 and 15, we have indicated N-Channel or P-Channel. The Thermal Impedance Graph (Fig. 11) is the only exception where a graph is common to both N-Channel and P-Channel devices since the thermal impedance is only dependent on the die size and package.

In Table A below, a legend is provided cross referencing the part number to its assigned alpha code. A given device will retain this alpha code for each device specific graph.

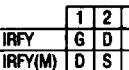
Table A

DEVICE	ALPHA DESIGNATION
IRFY044	a
IRFY120	b
IRFY130	c
IRFY140	d
IRFY240	e
IRFY340	f
IRFY430	g
IRFY440	h
IRFY9120	i
IRFY9130	j
IRFY9140	k
IRFY9240	l

IRFF Series Devices**HEXFET, CECC Qualified — Europe****T0257/HEXFET/N-Channel**

Basic Type	V_DS (V)	RDS(on) (Ohms)	CECC Specification	Issue No.	Issue Date	Level of Quality Assessment and CECC 50 000 Screen Level Options	Case Outline									
IRFY044(M)	60	0.03	50 012-062			E, EA, EB, EC, ED	T0-257AA Y-PAK  <table border="1" data-bbox="968 540 1123 610"> <tr> <td>1</td> <td>2</td> <td>3</td> </tr> <tr> <td>IRFY</td> <td>G</td> <td>D S</td> </tr> <tr> <td>IRFY(M)</td> <td>D</td> <td>S G</td> </tr> </table>	1	2	3	IRFY	G	D S	IRFY(M)	D	S G
1	2	3														
IRFY	G	D S														
IRFY(M)	D	S G														
IRFY120(M)	100	0.31	50 012-060			E, EA, EB, EC, ED										
IRFY130(M)	100	0.19	50 012-061			E, EA, EB, EC, ED										
IRFY140(M)	100	0.092	50 012-062	1	10/91	E, EA, EB, EC, ED										
IRFY240(M)	200	0.19	50 012-062			E, EA, EB, EC, ED										
IRFY340(M)	400	0.55	50 012-062			E, EA, EB, EC, ED										
IRFY430(M)	500	1.50	50 012-061			E, EA, EB, EC, ED										
IRFY440(M)	500	0.85	50 012-062			E, EA, EB, EC, ED										

T0257/HEXFET/P-Channel

IRFY9120(M)	-100	0.60	50 012-063			E, EA, EB, EC, ED	 <table border="1" data-bbox="968 558 1123 627"> <tr> <td>1</td> <td>2</td> <td>3</td> </tr> <tr> <td>IRFY</td> <td>G</td> <td>D S</td> </tr> <tr> <td>IRFY(M)</td> <td>D</td> <td>S G</td> </tr> </table>	1	2	3	IRFY	G	D S	IRFY(M)	D	S G
1	2	3														
IRFY	G	D S														
IRFY(M)	D	S G														
IRFY9130(M)	-100	0.31	50 012-064	1	10/91	E, EA, EB, EC, ED										
IRFY9140(M)	-100	0.21	50 012-065			E, EA, EB, EC, ED										
IRFY9240(M)	-200	0.50	50 012-065			E, EA, EB, EC, ED										

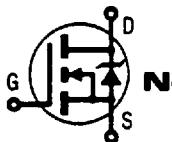
FOR OTHER GOVERNMENT/SPACE QUALIFIED PRODUCTS SEE SECTION E.

INTERNATIONAL RECTIFIER

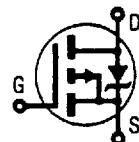


HEXFET® TRANSISTORS

IRFY SERIES



N-CHANNEL



P-CHANNEL

**IRFY044 THRU IRFY440
IRFY9120 THRU IRFY9240**

Description

The HEXFET® technology is the key to International Rectifier's advance line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance.

The HEXFET transistors also feature all of the well established advantages of MOSFET's such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies and virtually any application where military and/or high reliability is required.

The totally isolated package eliminates the need for additional isolating material between the device and the heatsink, this improves the thermal efficiency and reduces drain capacitance.

FEATURES

- Isolated and Hermetically Sealed
- Alternative to TO-39 and TO-66 Packages
- Simple Drive Requirements
- Ease of Paralleling
- Ceramic eyelet package used on all space level applications or on request

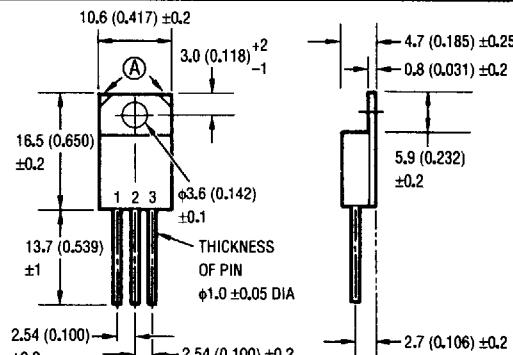
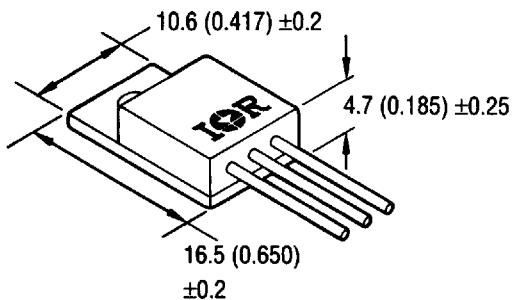
Product Summary N-Channel

Characteristic	IRFY044 thru IRFY440	Units
BVDSS	60 to 500	V
RDS(on)	0.035 to 1.6	Ω
ID	3.7 to 20	A

Product Summary P-Channel

Characteristic	IRFY9120 thru IRFY9240	Units
BVDSS	-100 to -200	V
RDS(on)	0.21 to 0.50	Ω
ID	-5.3 to -13	A

CASE STYLE AND DIMENSIONS



TERM	IRFY...	IRFY... M
1	GATE	DRAIN
2	DRAIN	SOURCE
3	SOURCE	GATE

(A) Corners removed to indicate 'M' option

Conforms to JEDEC Outline TO-257AB
Dimensions in Millimeters and (Inches)

N-CHANNEL — Absolute Maximum Ratings

Parameter	IRFY044	IRFY120	IRFY130	IRFY140	Unit
$I_D @ T_C = 25^\circ C$ Continuous Drain Current	20*	7.3	11	18	A
$I_D @ T_C = 100^\circ C$ Continuous Drain Current	20	4.6	7.0	12	A
I_{DM} Pulsed Drain Current	128	29	44	72	A
V_{GS} Gate-Source Voltage		± 20			V
$P_D @ T_C = 25^\circ C$ Maximum Power Dissipation	60	30	45	60	W
Linear Derating Factor	0.48	0.24	0.36	0.48	W/K
T_J Operating Junction Storage Temperature Range		-55 to 150			°C
T_{stg}					
Weight		3.4 (typical)			g

* I_D current limited by pin diameter**N-CHANNEL — Absolute Maximum Ratings (Continued)**

Parameter	IRFY240	IRFY340	IRFY430	IRFY440	Unit
$I_D @ T_C = 25^\circ C$ Continuous Drain Current	12	6.9	3.7	5.5	A
$I_D @ T_C = 100^\circ C$ Continuous Drain Current	7.8	4.4	2.4	3.5	A
I_{DM} Pulsed Drain Current	48	27	14	22	A
V_{GS} Gate-Source Voltage		± 20			V
$P_D @ T_C = 25^\circ C$ Maximum Power Dissipation	60	60	45	60	W
Linear Derating Factor	0.48	0.48	0.36	0.48	W/K
T_J Operating Junction Storage Temperature Range		-55 to 150			°C
T_{stg}					
Weight		3.4 (typical)			g

P-CHANNEL — Absolute Maximum Ratings

Parameter	IRFY9120	IRFY9130	IRFY9140	IRFY9240	Unit
$I_D @ T_C = 25^\circ C$ Continuous Drain Current	-5.3	-9.3	-13	-7.7	A
$I_D @ T_C = 100^\circ C$ Continuous Drain Current	-3.4	-5.8	-8.2	-4.9	A
I_{DM} Pulsed Drain Current	-21	-37	-52	-30	V
V_{GS} Gate-Source Voltage		± 20			V
$P_D @ T_C = 25^\circ C$ Maximum Power Dissipation	30	45	60	60	W
Linear Derating Factor	0.24	0.36	0.48	0.48	W/K
T_J Operating Junction Storage Temperature Range		-55 to 150			°C
T_{stg}					
Weight		3.4 (typical)			g

Electrical Characteristics @ $T_C = 25^\circ\text{C}$ (Unless otherwise specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	IRFY044	60	—	—	$I_D = 1.0\text{mA}, V_{GS} = 0\text{V}$
		IRFY120	100	—	—	
		IRFY130	100	—	—	
		IRFY140	100	—	—	
		IRFY240	200	—	—	
		IRFY340	400	—	—	
		IRFY430	500	—	—	
		IRFY440	500	—	—	
		IRFY9120	-100	—	—	
		IRFY9130	-100	—	—	
		IRFY9140	-100	—	—	
		IRFY9240	-200	—	—	
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	IRFY044	—	0.68	—	Reference to 25°C , $I_D = 1.0\text{mA}$
		IRFY120	—	0.1	—	
		IRFY130	—	0.1	—	
		IRFY140	—	0.1	—	
		IRFY240	—	0.29	—	
		IRFY340	—	0.46	—	
		IRFY430	—	0.78	—	
		IRFY440	—	0.78	—	
		IRFY9120	—	-0.1	—	
		IRFY9130	—	-0.1	—	
		IRFY9140	—	-0.087	—	
		IRFY9240	—	-0.20	—	
$R_{\text{DS(on)}}$	Static Drain-Source On-State Resistance	IRFY044	—	—	0.035	$V_{GS} = 10\text{V}$
		IRFY120	—	—	0.31	
		IRFY130	—	—	0.36	
		IRFY140	—	—	0.19	
		IRFY140	—	—	0.22	
		IRFY240	—	—	0.092	
		IRFY240	—	—	0.11	
		IRFY340	—	—	0.19	
		IRFY340	—	—	0.22	
		IRFY430	—	—	0.55	
		IRFY430	—	—	0.63	
		IRFY440	—	—	1.6	
		IRFY440	—	—	1.84	
		IRFY9120	—	—	0.85	
		IRFY9120	—	—	0.98	
		IRFY9130	—	—	0.60	
		IRFY9130	—	—	0.69	
		IRFY9140	—	—	0.31	$V_{GS} = -10\text{V}$
		IRFY9140	—	—	0.36	
		IRFY9140	—	—	0.21	
		IRFY9140	—	—	0.24	
$V_{GS(\text{th})}$	Gate Threshold Voltage	N-Channel	2.0	—	4.0	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
		P-Channel	-2.0	—	-4.0	

$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$

$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$

Electrical Characteristics (Continued)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
gfs Forward Transconductance	IRFY044	17	—	—	S(Ω)	I _D = 20A
	IRFY120	1.5	—	—		I _D = 4.6A
	IRFY130	3.0	—	—		I _D = 7.0A
	IRFY140	9.1	—	—		I _D = 12A
	IRFY240	6.1	—	—		V _{DS} ≥ 15V I _D = 7.8A
	IRFY340	4.9	—	—		I _D = 4.4A
	IRFY430	1.5	—	—		I _D = 2.4A
	IRFY440	4.7	—	—		I _D = 3.5A
	IRFY9120	1.25	—	—		I _D = -3.4A
	IRFY9130	2.5	—	—		V _{DS} ≥ -15V I _D = -5.8A
	IRFY9140	6.2	—	—		I _D = -8.2A
	IRFY9240	4.0	—	—		I _D = -4.9A
IDSS Zero Gate Voltage Drain Current	N-Channel	—	—	25	μA	V _{DS} = 0.8 x Max. Rating, V _{GS} = 0V
		—	—	250		V _{DS} = 0.8 x Max. Rating, V _{GS} = 0V, T _J = 25°C
	P-Channel	—	—	-25		V _{DS} = 0.8 x Max. Rating, V _{GS} = 0V
		—	—	-250		V _{DS} = 0.8 x Max. Rating, V _{GS} = 0V, T _J = 125°C
IGSS Gate-Source Leakage Forward	N-Channel	—	—	100	nA	V _{GS} = 20V
	P-Channel	—	—	-100		V _{GS} = -20V
IGSR Gate-Source Leakage Reverse	N-Channel	—	—	-100		V _{GS} = -20V
	P-Channel	—	—	100		V _{GS} = 20V
Qg Total Gate Charge (Gate-Source plus Gate-Drain)	IRFY044	39	—	88	nC	I _D = 20A
	IRFY120	7.7	—	17		I _D = 7.3A
	IRFY130	12.8	—	28.5		I _D = 11A
	IRFY140	30	—	59		I _D = 18A
	IRFY240	32	—	60		V _{GS} = 10V, V _{DS} = 0.5 x V _{DS} max. I _D = 12A
	IRFY340	32	—	65		I _D = 6.9A
	IRFY430	19.8	—	29.5		I _D = 3.7A
	IRFY440	27.3	—	68.5		I _D = 5.5A
	IRFY9120	4.3	—	16.3		I _D = -5.3A
	IRFY9130	14.7	—	30		V _{GS} = -10V, V _{DS} = 0.5 x V _{DS} max. I _D = -9.3A
	IRFY9140	31	—	60		I _D = -13A
	IRFY9240	28	—	60		I _D = -7.7A
Qgs Gate Source Charge	IRFY044	6.7	—	15	nC	I _D = 20A
	IRFY120	0.7	—	4.0		I _D = 7.3A
	IRFY130	1.0	—	6.3		I _D = 11A
	IRFY140	2.4	—	12		I _D = 18A
	IRFY240	2.2	—	10.6		V _{GS} = 10V, V _{DS} = 0.5 x V _{DS} max. I _D = 12A
	IRFY340	2.2	—	10		I _D = 6.9A
	IRFY430	2.2	—	4.6		I _D = 3.7A
	IRFY440	2.0	—	12.5		I _D = 5.5A
	IRFY9120	1.3	—	4.7		I _D = -5.3A
	IRFY9130	1.0	—	7.1		V _{GS} = -10V, V _{DS} = 0.5 x V _{DS} max. I _D = -9.3A
	IRFY9140	3.7	—	13		I _D = -13A
	IRFY9240	3.0	—	15		I _D = -7.7A

Electrical Characteristics (Continued)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
Qgd Gate Drain ("Miller") Charge	IRFY044	18	—	52	nC	$I_D = 20A$
	IRFY120	2.0	—	8.0		$I_D = 7.3A$
	IRFY130	3.8	—	16.6		$I_D = 11A$
	IRFY140	12	—	30.7		$I_D = 18A$
	IRFY240	14.2	—	37.6		$I_D = 12A$
	IRFY340	13.8	—	40.5		$I_D = 6.9A$
	IRFY430	5.5	—	19.7		$I_D = 3.7A$
	IRFY440	11.1	—	42.4		$I_D = 5.5A$
	IRFY9120	1.0	—	9.0		$I_D = -5.3A$
	IRFY9130	2.0	—	21		$V_{GS} = -10V$, $V_{DS} = 0.5 \times V_{DS} \text{ max.}$
	IRFY9140	7.0	—	35.2		$I_D = -9.3A$
	IRFY9240	4.5	—	38		$I_D = -13A$ $V_{DS} = V_{DS} \text{ max.} \times 0.8$
	IRFY9240	—	—	—		$I_D = -7.7A$
td(on) Turn-on Delay Time	IRFY044	—	—	23	ns	$V_{DD} = 30V, I_D = 20A, R_G = 9.1\Omega$
	IRFY120	—	—	15		$V_{DD} = 50V, I_D = 7.3A, R_G = 7.5\Omega$
	IRFY130	—	—	30		$V_{DD} = 50V, I_D = 11A, R_G = 7.5\Omega$
	IRFY140	—	—	21		$V_{DD} = 50V, I_D = 18A, R_G = 9.1\Omega$
	IRFY240	—	—	20		$V_{DD} = 100V, I_D = 12A, R_G = 9.1\Omega$
	IRFY340	—	—	25		$V_{DD} = 200V, I_D = 6.9A, R_G = 9.1\Omega$
	IRFY430	—	—	35		$V_{DD} = 250V, I_D = 3.7A, R_G = 7.5\Omega$
	IRFY440	—	—	21		$V_{DD} = 250V, I_D = 5.5A, R_G = 9.1\Omega$
	IRFY9120	—	—	60		$V_{DD} = -50V, I_D = -5.3A, R_G = 7.5\Omega$
	IRFY9130	—	—	60		$V_{DD} = -50V, I_D = -9.3A, R_G = 7.5\Omega$
	IRFY9140	—	—	35		$V_{DD} = -50V, I_D = -13A, R_G = 9.1\Omega$
	IRFY9240	—	—	35		$V_{DD} = -100V, I_D = -7.7A, R_G = 9.1\Omega$
tr Rise Time	IRFY044	—	—	130	ns	$V_{DD} = 30V, I_D = 20A, R_G = 9.1\Omega$
	IRFY120	—	—	70		$V_{DD} = 50V, I_D = 7.3A, R_G = 7.5\Omega$
	IRFY130	—	—	75		$V_{DD} = 50V, I_D = 11A, R_G = 7.5\Omega$
	IRFY140	—	—	145		$V_{DD} = 50V, I_D = 18A, R_G = 9.1\Omega$
	IRFY240	—	—	152		$V_{DD} = 100V, I_D = 12A, R_G = 9.1\Omega$
	IRFY340	—	—	92		$V_{DD} = 200V, I_D = 6.9A, R_G = 9.1\Omega$
	IRFY430	—	—	30		$V_{DD} = 250V, I_D = 3.7A, R_G = 7.5\Omega$
	IRFY440	—	—	73		$V_{DD} = 250V, I_D = 5.5A, R_G = 9.1\Omega$
	IRFY9120	—	—	100		$V_{DD} = -50V, I_D = -5.3A, R_G = 7.5\Omega$
	IRFY9130	—	—	140		$V_{DD} = -50V, I_D = -9.3A, R_G = 7.5\Omega$
	IRFY9140	—	—	85		$V_{DD} = -50V, I_D = -13A, R_G = 9.1\Omega$
	IRFY9240	—	—	85		$V_{DD} = -100V, I_D = -7.7, R_G = 9.1\Omega$
td(off) Turn-Off Delay Time	IRFY044	—	—	81	ns	$V_{DD} = 30V, I_D = 20A, R_G = 9.1\Omega$
	IRFY120	—	—	40		$V_{DD} = 50V, I_D = 7.3A, R_G = 7.5\Omega$
	IRFY130	—	—	40		$V_{DD} = 50V, I_D = 11A, R_G = 7.5\Omega$
	IRFY140	—	—	64		$V_{DD} = 50V, I_D = 18A, R_G = 9.1\Omega$
	IRFY240	—	—	58		$V_{DD} = 100V, I_D = 12A, R_G = 9.1\Omega$
	IRFY340	—	—	79		$V_{DD} = 200V, I_D = 6.9A, R_G = 9.1\Omega$
	IRFY430	—	—	55		$V_{DD} = 250V, I_D = 3.7A, R_G = 7.5\Omega$
	IRFY440	—	—	72		$V_{DD} = 250V, I_D = 5.5A, R_G = 9.1\Omega$
	IRFY9120	—	—	50		$V_{DD} = -50V, I_D = -5.3A, R_G = 7.5\Omega$
	IRFY9130	—	—	140		$V_{DD} = -50V, I_D = -9.3A, R_G = 7.5\Omega$
	IRFY9140	—	—	85		$V_{DD} = -50V, I_D = -13A, R_G = 9.1\Omega$
	IRFY9240	—	—	85		$V_{DD} = -100V, I_D = -7.7, R_G = 9.1\Omega$

Electrical Characteristics (Continued)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
t _f	IRFY044	—	—	79	ns	V _{DD} = 30V, I _D = 20A, R _G = 9.1Ω
	IRFY120	—	—	70		V _{DD} = 50V, I _D = 7.3A, R _G = 7.5Ω
	IRFY130	—	—	45		V _{DD} = 50V, I _D = 11A, R _G = 7.5Ω
	IRFY140	—	—	105		V _{DD} = 50V, I _D = 18A, R _G = 9.1Ω V _{GS} = 10V
	IRFY240	—	—	67		V _{DD} = 100V, I _D = 12A, R _G = 9.1Ω
	IRFY340	—	—	58		V _{DD} = 200V, I _D = 6.9A, R _G = 9.1Ω
	IRFY430	—	—	30		V _{DD} = 250V, I _D = 3.7A, R _G = 7.5Ω
	IRFY440	—	—	51		V _{DD} = 250V, I _D = 5.5A, R _G = 9.1Ω
	IRFY9120	—	—	70		V _{DD} = -50V, I _D = -5.3A, R _G = 7.5Ω
	IRFY9130	—	—	140		V _{DD} = -50V, I _D = -9.3A, R _G = 7.5Ω V _{GS} = -10V
	IRFY9140	—	—	65		V _{DD} = -50V, I _D = -13A, R _G = 9.1Ω
	IRFY9240	—	—	65		V _{DD} = -100V, I _D = -7.7A, R _G = 9.1Ω
L _D	Internal Drain Inductance	N-Channel	—	8.7	nH	Measured from the drain lead, 6 mm (0.25 in.) from package to center of die
L _S	Internal Source Inductance					Modified MOSFET symbol showing the internal inductances. 
L _D	Internal Drain Inductance	P-Channel	—	8.7	nH	Measured from the drain lead, 6 mm (0.25 in.) from package to center of die
L _S	Internal Source Inductance					Measured from the source lead, 6 mm (0.25 in.) from package to center of source bonding pad
C _{iss}	Input Capacitance	IRFY044	—	2400	pF	V _{GS} = 0V, V _{DS} = 25V, f = 1.0 MHz See fig. 5
		IRFY120	—	350		
		IRFY130	—	650		
		IRFY140	—	1660		
		IRFY240	—	1300		
		IRFY340	—	1400		
		IRFY430	—	610		
		IRFY440	—	1300		
		IRFY9120	—	380		
		IRFY9130	—	800		
		IRFY9140	—	1400		
		IRFY9240	—	1200		
C _{oss}	Output Capacitance	IRFY044	—	1100	pF	V _{GS} = 0V, V _{DS} = 25V, f = 1.0 MHz See fig. 5
		IRFY120	—	150		
		IRFY130	—	240		
		IRFY140	—	550		
		IRFY240	—	400		
		IRFY340	—	350		
		IRFY430	—	135		
		IRFY440	—	310		
		IRFY9120	—	170		
		IRFY9130	—	350		
		IRFY9140	—	600		
		IRFY9240	—	570		

Electrical Characteristics (Continued)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
Crss Reverse Transfer Capacitance	IRFY044	—	230	—	pF	VGS = 0V, VDS = 25V, f = 1.0 MHz See fig. 5
	IRFY120	—	24	—		
	IRFY130	—	44	—		
	IRFY140	—	120	—		
	IRFY240	—	130	—		
	IRFY340	—	230	—		
	IRFY430	—	65	—		
	IRFY440	—	120	—		
	IRFY9120	—	45	—		
	IRFY9130	—	125	—		
	IRFY9140	—	200	—		
	IRFY9240	—	81	—		

Source-Drain Diode Rating and Characteristics

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
Is Continuous Source Current (Body Diode)	IRFY044	—	—	20	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
	IRFY120	—	—	7.3		
	IRFY130	—	—	11		
	IRFY140	—	—	18		
	IRFY240	—	—	12		
	IRFY340	—	—	6.9		
	IRFY430	—	—	3.7		
	IRFY440	—	—	5.5		
	IRFY9120	—	—	-5.3		
	IRFY9130	—	—	-9.3		
	IRFY9140	—	—	-13		
	IRFY9240	—	—	-7.7		
ISM Pulsed Source Current (Body Diode)	IRFY044	—	—	128	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
	IRFY120	—	—	29		
	IRFY130	—	—	43		
	IRFY140	—	—	73		
	IRFY240	—	—	49		
	IRFY340	—	—	27		
	IRFY430	—	—	14		
	IRFY440	—	—	22		
	IRFY9120	—	—	-21		
	IRFY9130	—	—	-37		
	IRFY9140	—	—	-52		
	IRFY9240	—	—	-30		

Source-Drain Diode Ratings and Characteristics (Continued)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions	
VSD	Diode Forward Voltage	IRFY044	—	—	2.5	V	I _S = 20A	T _C = 25°C, V _{GS} = 0V
		IRFY120	—	—	1.8		I _S = 7.3A	
		IRFY130	—	—	1.5		I _S = 11A	
		IRFY140	—	—	1.5		I _S = 18A	
		IRFY240	—	—	1.5		I _S = 12A	
		IRFY340	—	—	1.5		I _S = 6.9A	
		IRFY430	—	—	1.4		I _S = 3.7A	
		IRFY440	—	—	1.5		I _S = 5.5A	
		IRFY9120	—	—	-4.8		I _S = -5.3A	
		IRFY9130	—	—	-4.7		I _S = -9.3A	
		IRFY9140	—	—	-4.2		I _S = -13A	
		IRFY9240	—	—	-4.6		I _S = -7.7A	
t _{rr}	Reverse Recovery Time	IRFY044	—	—	220	ns	I _F = 20A	T _J = 25°C, di/dt ≤ 100A/μs V _{DD} ≤ 50V
		IRFY120	—	—	240		I _S = 7.3A	
		IRFY130	—	—	300		I _S = 11A	
		IRFY140	—	—	400		I _S = 18A	
		IRFY240	—	—	500		I _S = 12A	
		IRFY340	—	—	600		I _S = 6.9A	
		IRFY430	—	—	900		I _S = 3.7A	
		IRFY440	—	—	700		I _S = 5.5A	
		IRFY9120	—	—	200		I _S = -5.3A	
		IRFY9130	—	—	250		I _S = -9.3A	
		IRFY9140	—	—	280		I _S = -13A	
		IRFY9240	—	—	440		I _S = -7.7A	

Source-Drain Diode Ratings and Characteristics (Continued)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
Q_{rr} Reverse Recovered Charge	IRFY044	—	—	1.6	μC	$I_S = 20\text{A}$
	IRFY120	—	—	2.0		$I_S = 7.3\text{A}$
	IRFY130	—	—	3.0		$I_S = 11\text{A}$
	IRFY140	—	—	2.4		$I_S = 18\text{A}$ $T_J = 25^\circ\text{C}$, $di/dt \leq 100\text{A}/\mu\text{s}$
	IRFY240	—	—	5.3		$I_S = 12\text{A}$ $V_{DD} \leq 50\text{V}$
	IRFY340	—	—	5.6		$I_S = 6.9\text{A}$
	IRFY430	—	—	7.0		$I_S = 3.7\text{A}$
	IRFY440	—	—	8.9		$I_S = 5.5\text{A}$
	IRFY9120	—	—	3.1		$I_S = -5.3\text{A}$
	IRFY9130	—	—	3.0		$I_S = -9.3\text{A}$ $T_J = 25^\circ\text{C}$, $di/dt \leq -100\text{A}/\mu\text{s}$
	IRFY9140	—	—	3.6		$I_S = -13\text{A}$ $V_{DD} \leq -50\text{V}$
	IRFY9240	—	—	7.2		$I_S = -7.7\text{A}$

Thermal Resistance and Isolation

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
R _{thJC}	Junction-to-Case	IRFY044	—	—	2.1	K/W	
		IRFY120	—	—	4.1		
		IRFY130	—	—	2.8		
		IRFY140	—	—	2.1		
		IRFY240	—	—	2.1		
		IRFY340	—	—	2.1		
		IRFY430	—	—	2.8		
		IRFY440	—	—	2.1		
		IRFY9120	—	—	4.1		
		IRFY9130	—	—	2.8		
		IRFY9140	—	—	2.1		
		IRFY9240	—	—	2.1		
R _{thCS}	Case-to-Sink	ALL	—	0.21	—	K/W	Mounting surface flat, smooth
R _{thJA}	Junction-to-Ambient	ALL	—	—	80	K/W	Typical socket mount